MA57

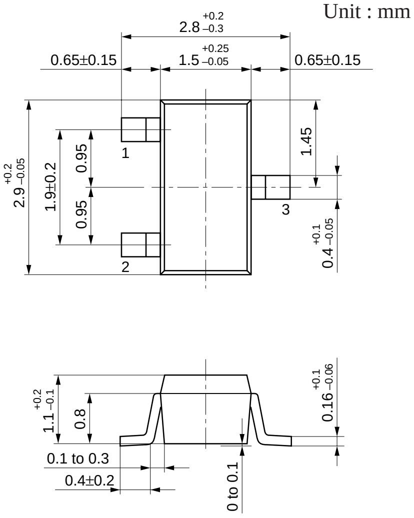
Silicon epitaxial planer type

For band switching

■ Features

- ● Low forward dynamic resistance r_f
- ● Less voltage dependence of diode capacity C_D
- ● Mini package, enabling down-sizing of the equipment and automatic insertion through taping

Unit : mm



1 : Anode
2 : NC JEDEC : TO-236
3 : Cathode EIAJ : SC-59A
Mini Type Package (3-pin)

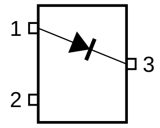
Marking Symbol : MX

■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	35	V
Forward current (DC)	I_F	100	mA
Operating ambient temperature	T_{opr}*	– 25 to + 85	˚C
Storage temperature	T_{stg}	– 55 to +150	˚C

* Maximum ambient temperature during operation

■ Internal Connection

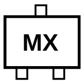


■ Electrical Characteristics (Ta= 25˚C)

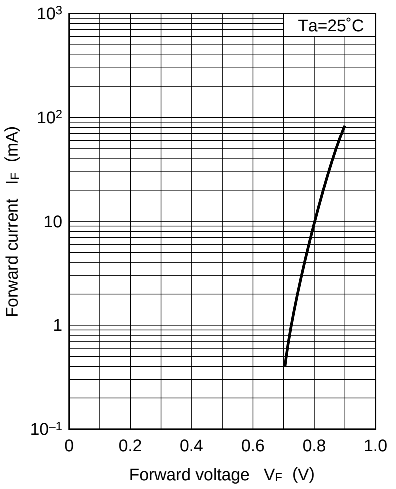
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R= 33V		0.01	100	nA
Forward voltage (DC)	V_F	I_F=100mA		0.88	1.0	V
Diode capacitance	C_D	V_R= 15V, f=1MHz		1.3	2.0	pF
Forward dynamic resistance	r_f *	I_F= 3mA, f=100MHz		0.78	1.15	Ω

Note 1 : Rated input/output frequency : 100MHz
2 : * r_f measurement device : YHP MODEL 4191A RF IMPEDANCE ANALYZER

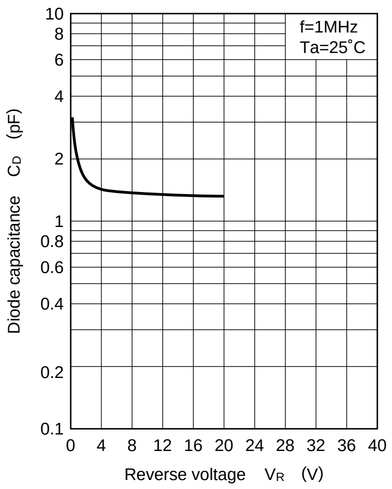
■ Marking



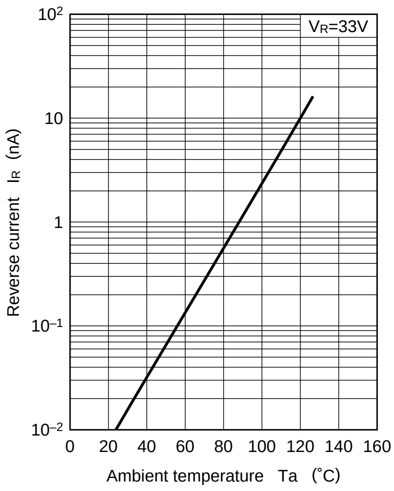
$I_F - V_F$



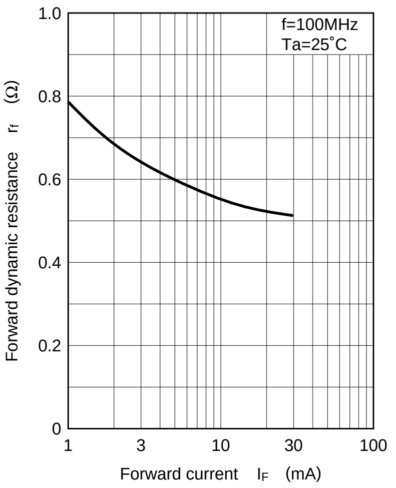
$C_D - V_R$



$I_R - Ta$



$r_f - I_F$



$r_f - f$